



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re the Application of: **IMANISHI, Kenji**

Serial No.: **09/981,842**

Filed: **October 19, 2001**

For: **FIELD-EFFECT TRANSISTOR USING A GROUP III-IV COMPOUND SEMICONDUCTOR**

Group Art Unit: **2815**

Examiner: **BAUMEISTER, Bradley**

P.T.O. Confirmation No.: **7067**

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AMENDMENT UNDER 37 CFR §1.111

Commissioner for Patents

Washington, D.C. 20231

Sir:

December 30, 2002

In response to the Office Action dated **October 1, 2002**, please amend the above-identified application as follows:

IN THE CLAIMS:

Please amend claims 1, 3, 8, and 9 as follows:

1. (Amended) A high electron mobility transistor using a Group III-V compound semiconductor, comprising
- an undoped second channel layer laminated on an InP substrate via a buffer layer;
- an undoped first channel layer laminated on said second channel layer; and
- a doped electron-supplying layer laminated on said first channel layer,
- wherein said first channel layer is composed of $\text{In}_{1-x}\text{Ga}_x\text{As}$ and has an energy layer level of conduction band lower than that of said electron-supplying layer,
- said second channel layer is composed of a Group III-V compound semiconductor